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MPF102

Preferred Devices

JFET VHF Amplifier

N−Channel − Depletion

ON Semiconductor®

http://onsemi.com

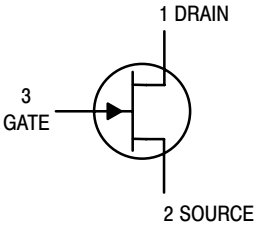
Features

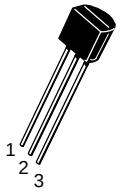
- Pb−Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain−Source Voltage	V_{DS}	25	Vdc
Drain−Gate Voltage	V_{DG}	25	Vdc
Gate−Source Voltage	V_{GS}	−25	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 350 2.8	 mW mW/°C
Junction Temperature Range	T_J	125	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

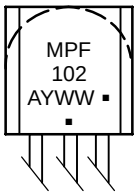
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.





TO−92 (TO−226AA)
CASE 29−11
STYLE 5

MARKING DIAGRAM



MPF102 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
MPF102	TO−92	1000 Units/Bulk
MPF102G	TO−92 (Pb−Free)	1000 Units/Bulk

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate−Source Breakdown Voltage (I_G = −10 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	−25	−	Vdc
Gate Reverse Current (V_{GS} = −15 Vdc, V_{DS} = 0) (V_{GS} = −15 Vdc, V_{DS} = 0, T_A = 100°C)	I_{GSS}	− −	−2.0 −2.0	nAdc μAdc
Gate−Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 2.0 nAdc)	$V_{GS(off)}$	−	−8.0	Vdc
Gate−Source Voltage (V_{DS} = 15 Vdc, I_D = 0.2 mAdc)	V_{GS}	−0.5	−7.5	Vdc
ON CHARACTERISTICS				
Zero−Gate−Voltage Drain Current (Note 1) (V_{DS} = 15 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	2.0	20	mAdc
SMALL−SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (Note 1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	$\lvert y_{fs} \rvert$	2000 1600	7500 −	μmhos
Input Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	$Re(y_{is})$	−	800	μmhos
Output Conductance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	$Re(y_{os})$	−	200	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	−	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	−	3.0	pF

1. Pulse Test; Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

COMMON SOURCE CHARACTERISTICS

ADMITTANCE PARAMETERS

(V_{DS} = 15 Vdc, $T_{channel}$ = 25°C)

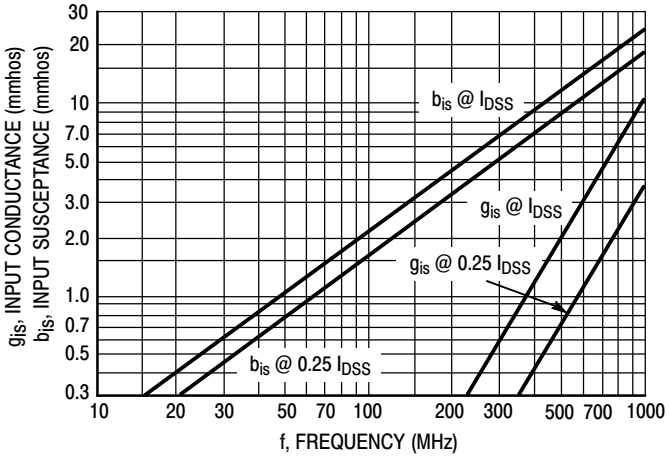


Figure 1. Input Admittance (y_{is})

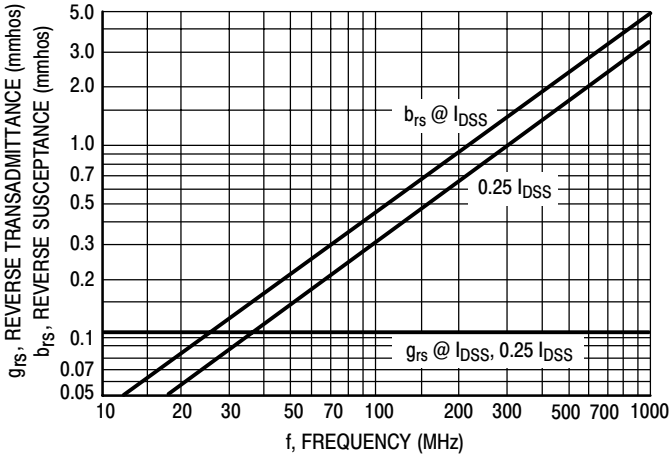


Figure 2. Reverse Transfer Admittance (y_{rs})

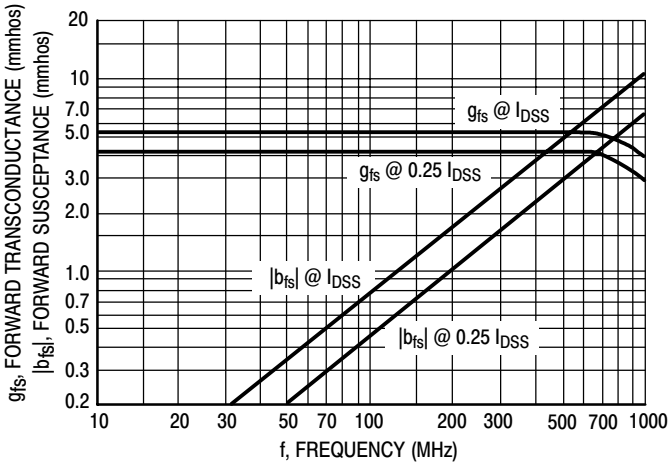


Figure 3. Forward Transfer Admittance (y_{fs})

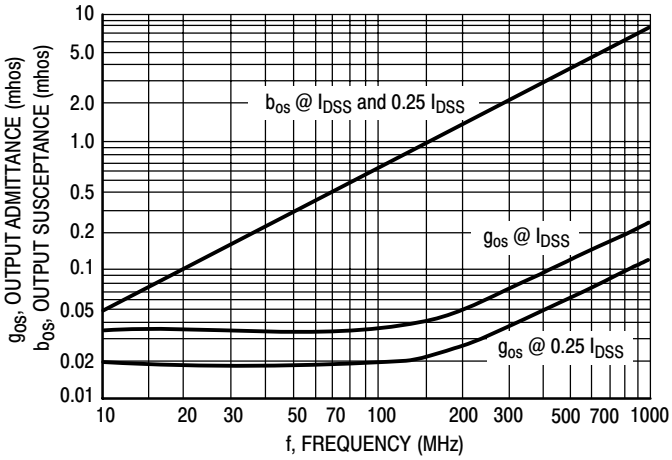


Figure 4. Output Admittance (y_{os})

COMMON SOURCE CHARACTERISTICS

S−PARAMETERS

(V_{DS} = 15 Vdc, $T_{channel}$ = 25°C, Data Points in MHz)

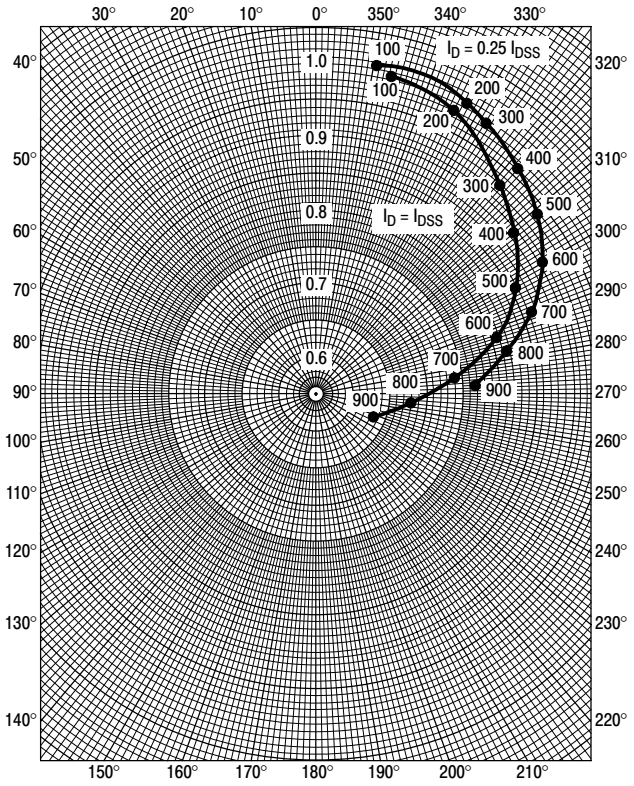


Figure 5. S_{11s}

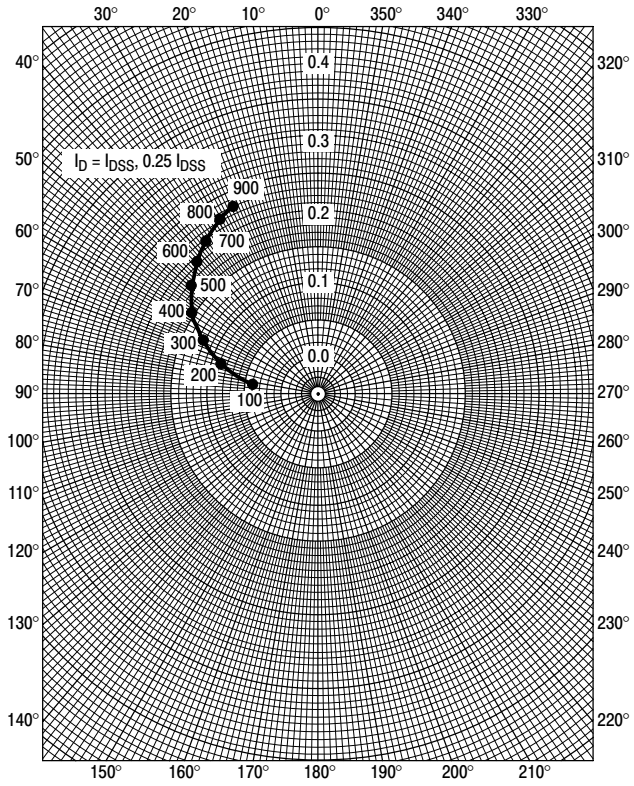


Figure 6. S_{12s}

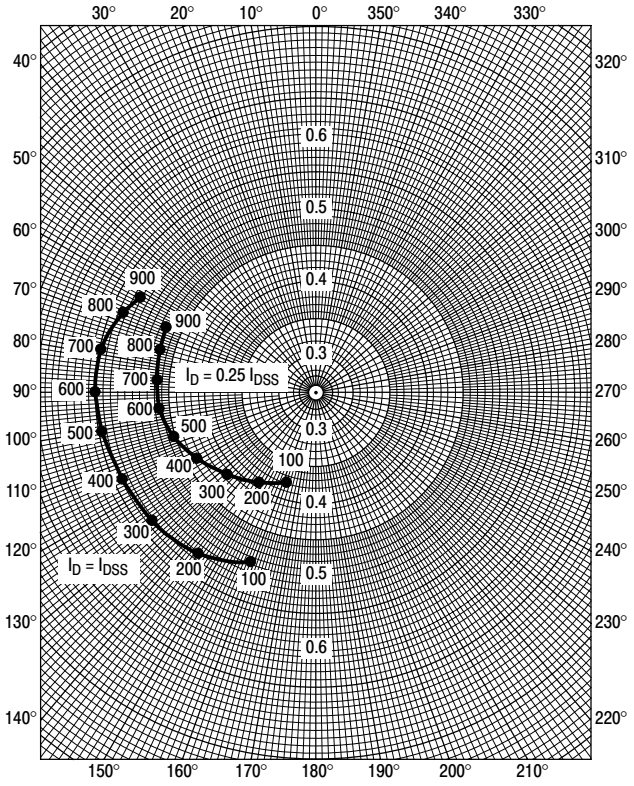


Figure 7. S_{21s}

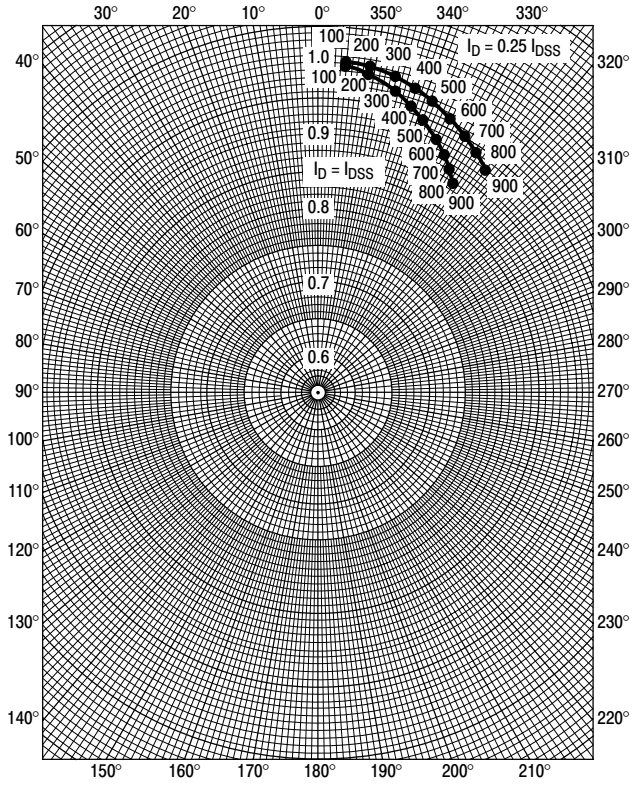


Figure 8. S_{22s}

COMMON GATE CHARACTERISTICS

ADMITTANCE PARAMETERS

(V_{DG} = 15 Vdc, $T_{channel}$ = 25°C)

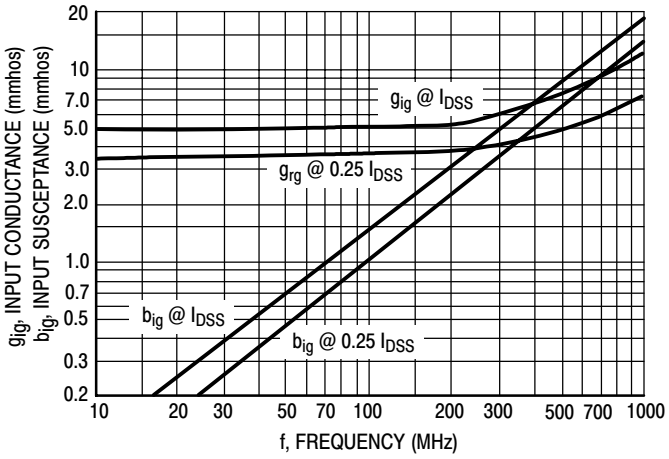


Figure 9. Input Admittance (y_{ig})

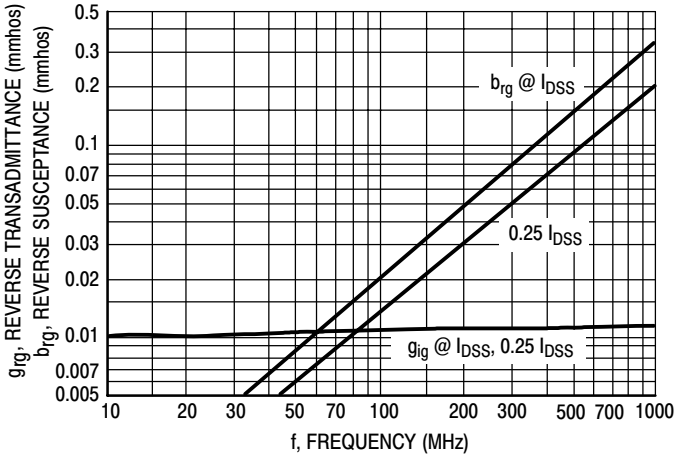


Figure 10. Reverse Transfer Admittance (y_{rg})

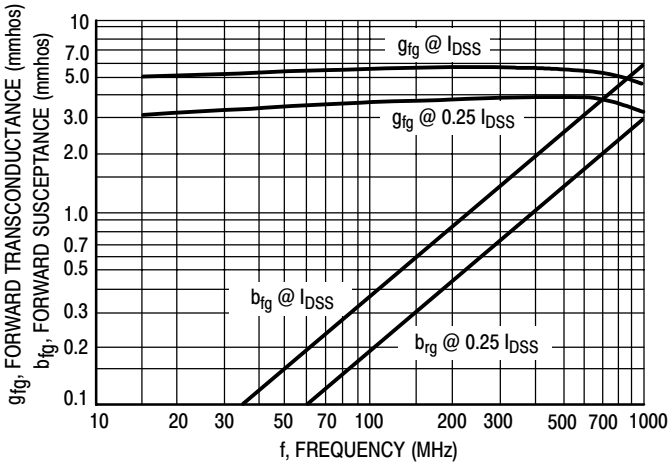


Figure 11. Forward Transfer Admittance (y_{fg})

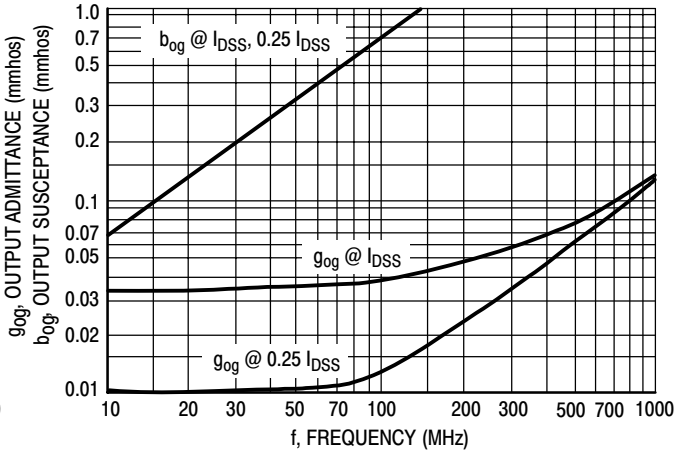


Figure 12. Output Admittance (y_{og})

COMMON GATE CHARACTERISTICS

S−PARAMETERS

(V_{DS} = 15 Vdc, $T_{channel}$ = 25°C, Data Points in MHz)

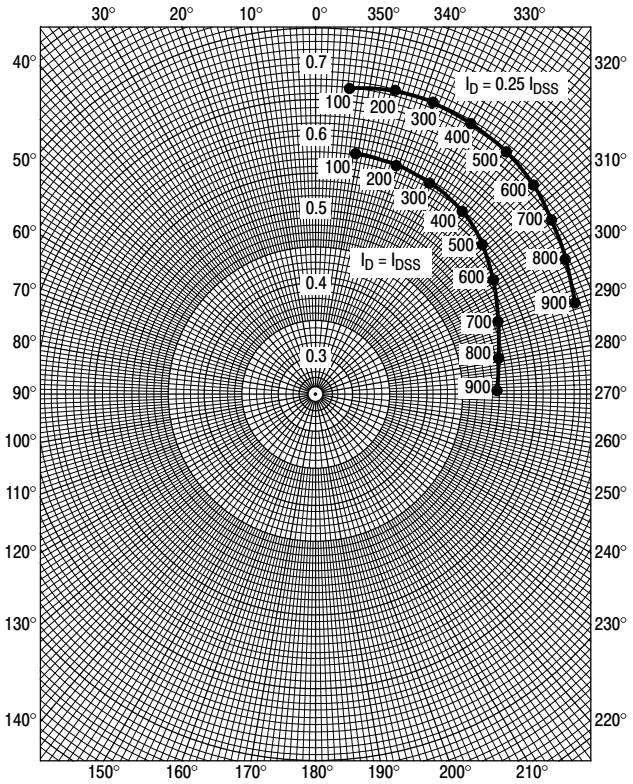


Figure 13. S_{11g}

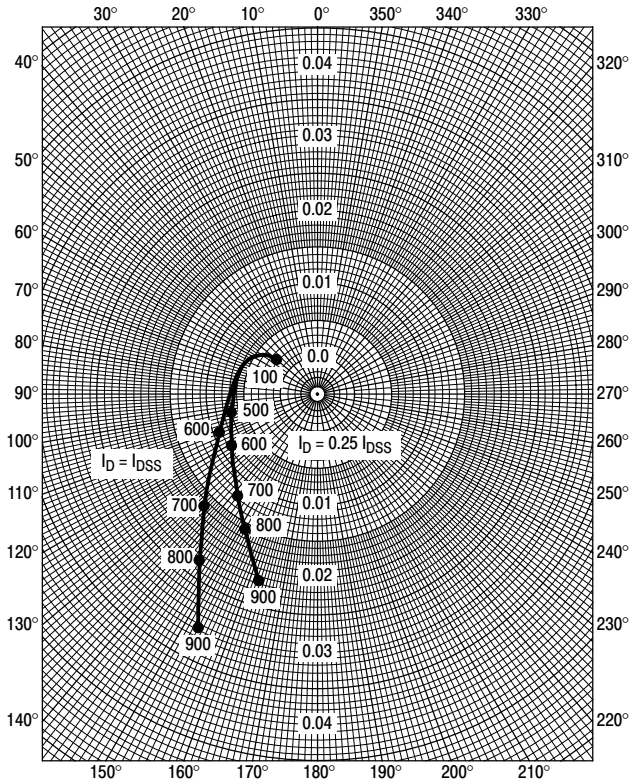


Figure 14. S_{12g}

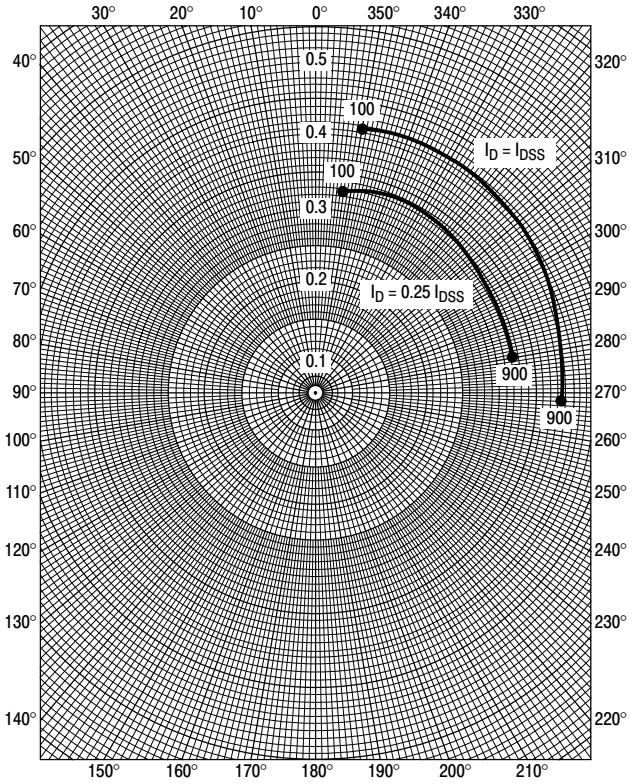


Figure 15. S_{21a}

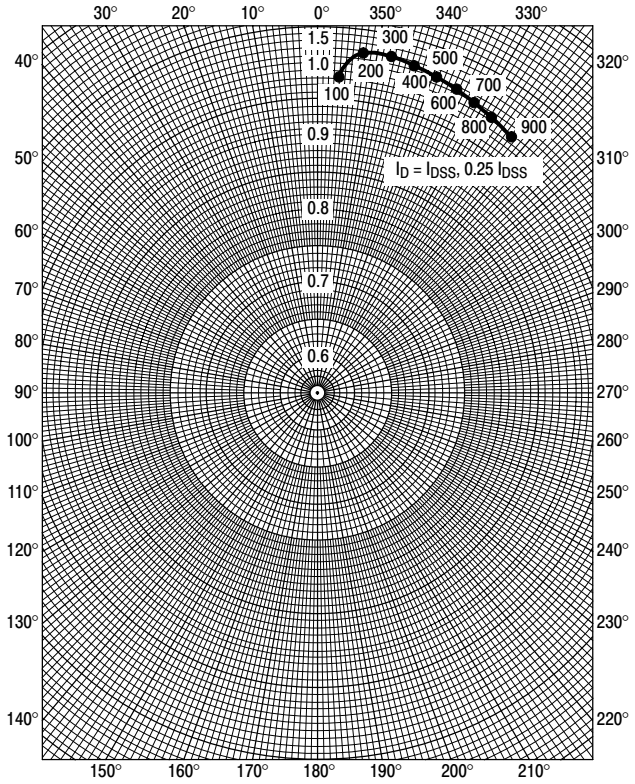
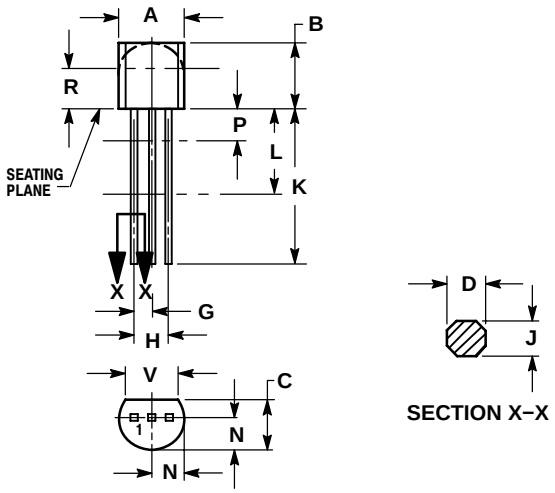


Figure 16. S_{22a}

PACKAGE DIMENSIONS

TO−92 (TO−226)
CASE 29−11
ISSUE AL



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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MPF102/D